

What is claimed is:

1 1. A method for forming a semiconductor device, comprising:
2 forming a first pattern for a semiconductor device in a semiconductor
3 device formation region of a semiconductor substrate and simultaneously
4 forming the first pattern in a first mark formation region of the semiconductor
5 substrate;
6 forming a second pattern for the semiconductor device on a resultant
7 structure in the semiconductor device formation region of the semiconductor
8 substrate and simultaneously forming the second pattern in a second mark
9 formation region of the semiconductor substrate; and
10 inspecting the first pattern in the first mark formation region and the
11 second pattern in the second mark formation region for misalignments.

1 2. The method for forming a semiconductor device as claimed in
2 claim 1, wherein the first mark formation region is a box shaped main scale
3 formation region, and the second mark formation region is a box shaped
4 vernier formation region.

1 3. The method for forming a semiconductor device as claimed in
2 claim 2, wherein the first pattern is an active pattern in a DRAM cell region,
3 and the second pattern is a word line pattern in the DRAM cell region.

1 4. The method for forming a semiconductor device as claimed in
2 claim 1, wherein a scattering bar is formed at an edge of a pattern in a mask
3 corresponding to the first pattern in the first mark formation region.

1 5. The method for forming a semiconductor device as claimed in
2 claim 1, wherein a scattering bar is formed at an edge of a pattern in a mask
3 corresponding to the second pattern in the second mark formation region.

1 6. A semiconductor device having an overlay mark, the overlay
2 mark, comprising:

3 a first mark formed in a first mark formation region of a semiconductor
4 substrate and a first pattern formed in a semiconductor device formation region
5 of the semiconductor substrate, wherein the first mark and the first pattern are
6 formed simultaneously by a same process such that the first mark has a shape
7 identical to a shape of the first pattern; and

8 a second mark formed in a second mark formation region of the
9 semiconductor substrate and a second pattern formed in the semiconductor
10 device formation region of the semiconductor substrate, wherein the second
11 mark and the second pattern are formed simultaneously by a same process
12 such that the second mark has a shape identical to a shape of the second
13 pattern.

1 7. The semiconductor device as claimed in claim 6, wherein the
2 first mark formation region is a box shaped main scale formation region, and
3 the second mark formation region is a box shaped vernier formation region.

1 8. The semiconductor device as claimed in claim 7, wherein the
2 first pattern is an active pattern in a DRAM cell region, and the second pattern
3 is a word line pattern in the DRAM cell region.